

STMUX7000

7-channel MUX/DEMUX for analog video signal

Features

- Low R_{ON}: 4.0 Ω typical
- V_{CC} operating range: 3.0 to 3.6 V
- Enhanced ESD protection: > 8 kV (contact) and 8 kV (HBM)
- Channel on capacitance: 7.8 pF typical
- Designed for VGA signal switching
- Integrated switches for RGB, HSYNC, VSYNC and DDC signals
- Very low crosstalk: -45 dB at 250 MHz
- > 1000 MHz -3 dB typical bandwidth (or data frequency)
- Low power mode for minimum power consumption
- Package: QFN32L

Applications

Audio/video switching ybsolete P



Description

The STMUX7000 is a 7-channel multiplexer/demultiplexer low RON bidirectional designed for analog video signal, such as VGA. It is designed for very low crosstalk, and high bandwidth to maintain high signal integrity.

The analog video signal multiplexed from one of two selected sources in the notebook and docking station while the unselected switch goes to Hi-Z status.

The device is also protected against high ESD that supports up to 8 kV contact on all I/O pins.

The device can be put into low power mode consuming minimum power.

Table 1. **Device summary**

Order code	Package	Packing	
STMUX7000QTR	QFN32 (3 x 6 x 0.8 mm)	Tape and reel	

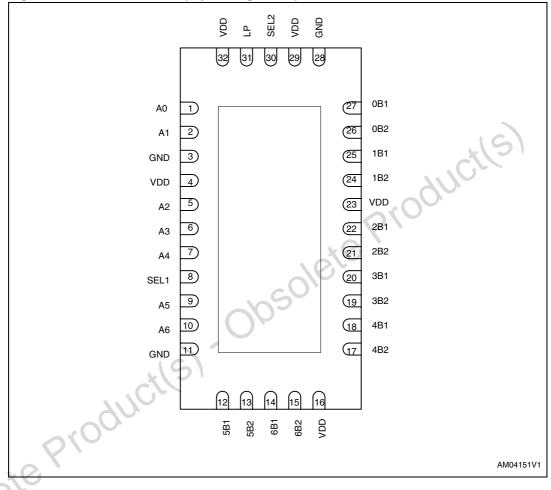
Contents

1	Pin description
2	Maximum rating 5 2.1 Recommended operating conditions 5
3	Electrical characteristics
4	Package mechanical data14
5	Revision history
obsc	Pin description 3 Maximum rating 5 2.1 Recommended operating conditions 5 Electrical characteristics 6 Package mechanical data 14 Revision history 18



Pin description 1

Figure 1. Pin connection (top through view)



Pin description

	. O. ^K		AM04151V1
26	Table 2. Pin description		
- SU!	Pin	Symbol	Name and function
$O_{\mathcal{P}}$	8	SEL 1	Selecion for bit 0, 1, 2, 3, 4
	30	SEL 2	Selection for bit 5, 6
	1, 2, 5, 6, 7, 9, 10	A0, A1, A2, A3, A4, A5, A6	8-bit bus
	4, 16, 23, 29, 32	VDD	Supply voltage
	3, 11, 28	GND	Ground
	27, 25, 22, 20, 18, 14, 12	0B1, 1B1, 2B1, 3B1, 4B1, 5B1, 6B1	8-bit multiplexed to bus 1
	26, 24, 21, 19, 17, 15, 13	0B2, 1B2, 2B2, 3B2, 4B2, 5B2, 6B2	8-bit multiplexed to bus 2
	31	LP	Low power mode enable



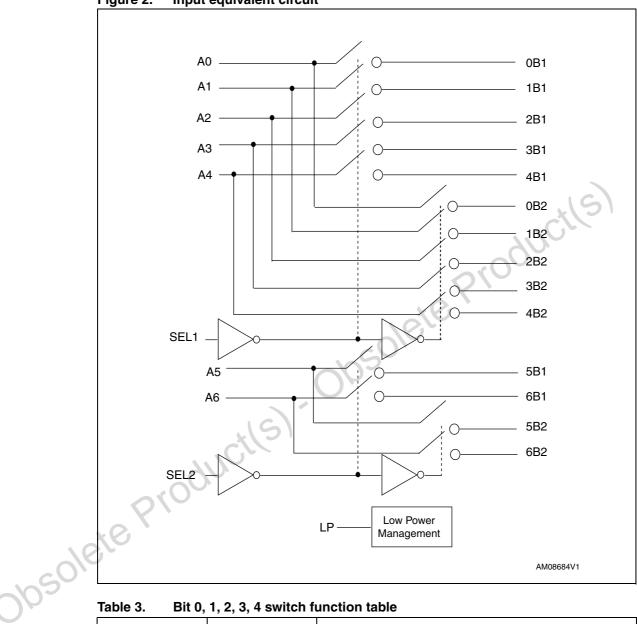


Figure 2. Input equivalent circuit

Table 3. Bit 0, 1, 2, 3, 4 switch function table

LP	SEL 1	Function
L	L	Bit 0, 1, 2, 3, 4 multiplexed to bus 1, bus 2 in Hi-Z
L	Н	Bit 0, 1, 2, 3, 4 multiplexed to bus 2, bus 1 in Hi-Z
Н	Х	Bus 1 and 2 in Hi-Z

Table 4. Bit 5, 6 switch function table

LP	SEL 2	Function
L	L	Bit 5,6 multiplexed to bus 1, bus 2 in Hi-Z



LP	SEL 2	Function
L	Н	Bit 5,6 multiplexed to bus 2, bus 1in Hi-Z
Н	х	Bus 1 and 2 in Hi-Z

Table 4.Bit 5, 6 switch function table



obsolete Product(s). Obsolete Product(s)

2 Maximum rating

Stressing the device above the rating listed in the "absolute maximum ratings" table may cause permanent damage to the device. These are stress ratings only and operation of the device at these or any other conditions above those indicated in the operating sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Symbol	Parameter	Value	Unit
V _{CC}	Supply voltage to ground	-0.5 to 4.6	V
V _{IO}	DC input output voltage	-0.5 to 4.6	V
V _{IC}	DC control input voltage	-0.5 to 4.6	V
۱ ₀	DC output current ⁽¹⁾	120	mA
PD	Power dissipation	0.5	W
T _{stg}	Storage temperature	-65 to 150	°C
TL	Lead temperature (10 sec)	300	°C

 Table 5.
 Absolute maximum ratings

1. If $V_{IO} \times I_O$ does not exceed the maximum limit of P_D .

2.1 Recommended operating conditions

Table 6. Recommended operating conditions

	Symbol	Parameter		Value		Unit
	Symbol		Min	Тур	Max	Unit
	V _{CC}	Supply voltage to ground	3	-	3.6	V
10	V _{IC}	DC control input voltage (SEL, LP)	0	-	5	V
cO^{\prime}	V _{IO}	DC input/output voltage	0	-	V _{CC}	V
05	T _A	Operating temperature	-40	-	85	°C
U ^r						



3 Electrical characteristics

				Value		
Symbol	Parameter	Test condition		-40 to 85 °C	;	Unit
			Min	Тур	Мах	
V _{IH}	Voltage input high (SEL, LP)	High level guaranteed	2	-	-	V
V _{IL}	Voltage input low (SEL, LP)	Low level guaranteed	-0.5	-	0.8	51
V _{IK}	Clamp diode voltage (SEL, LP)	I _{IN} = -18 mA		-0.8	-1.2	V
IIH	Input high current (SEL, LP)	$V_{CC} = 3.6 V$ $V_{IN} = V_{CC}$	-	<u>81</u>	±5	μA
Ι _{ΙL}	Input low current (SEL, LP)	$V_{CC} = 3.6 V$ $V_{IN} = GND$ ± 5		μA		
IOFF _(SW) ⁽¹⁾	Leakage current through the switch common terminals (A to H) (LED1 to LED3)	$V_{CC} = 3.6 V$ A to H = V _{CC} LED1 to LED3 = V _{CC} A0 to H0 = 0 V A1 to H1 = floating LEDx_0 = 0 V LEDx1 = floating SEL = V _{CC}	-	-	±1	μΑ
IOFF _{(SEL,} LP)	SEL, LP pin leakage current	V _{CC} = 0 V SEL = 0 to 3.6 V	-	-	±1	μA
R _{ON}	Switch ON resistance ⁽²⁾	V _{CC} = 3.0 V V _{IN} = 0 to 1.2 V I _{IN} = -40 mA	-	4.0	6.5	Ω
R _{FLAT}	ON resistance flatness ⁽²⁾	$V_{CC} = 3.0 V$ V_{IN} at 0 and 1.2V $I_{IN} = -40 mA$	-	0.5	-	Ω
ΔR_{ON}	ON resistance match between channel $\Delta R_{ON} = R_{ONMAX} - R_{ONMIN}$ (2)(4)	$V_{CC} = 3.0 V$ $V_{IN} = 0 \text{ to } 1.2 V$ $I_{IN} = -40 \text{ mA}$	-	0.4	1	Ω

Table 7. DC electrical characteristics ($V_{CC} = 3.3 \text{ V} \pm 10\%$)

1. Refer to Figure 4: Test circuit for leakage current (IOFF) on page 10

2. Measured by voltage drop between channels at indicated current through the switch. ON resistance is determined by the lower of the voltages.

3. Flatness is defined as the difference between the R_{ONMAX} and R_{ONMIN} of ON resistance over the specified range.

4. ΔR_{ON} measured at same V_{CC}, temperature and voltage level.



Table 0.	able 8. Capacitance ($T_A = 25^{\circ}C, T = T MHZ$)								
Symbol	Demonstern	To show distant		11					
Symbol	Parameter	Test condition	Min	Тур	Max	Unit			
C _{IN}	SEL, LP pin input capacitance ⁽¹⁾	DC = 0.25 V AC = 0.5 V _{PP} f = 1 MHz	-	2	3	pF			
C _{OFF}	Switch off capacitance ⁽²⁾	DC = 0.25 V AC = 0.5 V _{PP} f = 1 MHz	-	2.8	6.5	pF			
C _{ON}	Switch on capacitance ⁽³⁾	DC = 0.25 V AC = 0.5 V _{PP} f = 1 MHz	-	7.8	d	P F			
1. Refer to	Figure 5 on page 11.			2	5				
2. Refer to	Figure 6 on page 11.			×0V					
3. Refer to	3. Refer to Figure 7 on page 12.								
Table 9.	Table 9. Power supply characteristics								
		26		Value					

Capacitance ($T_{A} = 25 \,^{\circ}C_{c}$ f = 1 MHz) Table 8

Table 9. Power supply characteristics

Symbol	Parameter	Test condition	-	Unit		
		0*	Min	Тур	Max	
I _{CC}	Active mode power supply current	$V_{CC} = 3.6 \text{ V}, V_{IN} = V_{CC} \text{ or}$ GND, LP = GND	-	150	500	μA
I _{CC}	Low power mode power supply current	$V_{CC} = 3.6 \text{ V}, V_{IN} = V_{CC} \text{ or}$ GND, LP = V_{CC}	-	10	15	μA

Dynamic electrical characteristics (V_{CC} = 3.3 V ±10%) Table 10.

					Value		
26	Symbol	Parameter	Test condition	-40 to 85 °C		Unit	
ansu.				Min	Тур	Мах	
00	X _{talk}	Crosstalk ⁽¹⁾	$R_L = 50 \Omega$, $R_S = 50 \Omega$ f = 250 MHz	-	-45	-	dB
	O _{IRR}	Off isolation ⁽²⁾	$R_L = 50 \Omega$, $R_S = 50 \Omega$ f = 250 MHz	-	-32	-	dB
	BW	-3 dB bandwidth ⁽³⁾	$R_L = 50 \Omega$, $R_S = 50 \Omega$ 0 < V _{IN} ≤1.2 V	-	1000	-	MHz

1. Refer to Figure 9 on page 13.

2. Refer to Figure 10 on page 14.

3. Refer to *Figure 8 on page 12*.



Table 11. Switching characteristics ($I_A = 25$ °C, $V_{CC} = 3.3$ V ±10%)						
Symbol	Demonstern	Test sendition	Value			
Symbol	Parameter	Test condition	Min		Max	Unit
t _{PD}	Propagation delay	V _{CC} = 3 to 3.6 V	-	0.25	-	ns
t _{PZH} , t _{PZL}	Line enable time, SE to x to x0 or x to x1	$V_{CC} = 3 \text{ to } 3.6 \text{ V}$ 1 K Ω pull up/down resistor at xb1 or xB2	0.5	6.5	15	ns
t _{PHZ} , t _{PLZ}	Line disable time, SE to x to x0 or x to x1	$V_{CC} = 3 \text{ to } 3.6 \text{ V}$ 1 K Ω pull up/down resistor at xb1 or xB2	0.5	16		ns
t _{SK(O)}	Output skew between center port to any other port	V _{CC} = 3 to 3.6 V	-	0.1	0.2	ns
t _{SK(P)}	Skew between opposite transition of the same output (t _{PHL} , t _{PLH})	V _{CC} = 3 to 3.6 V	<u>-</u> <i>P</i>	0.1	0.2	ns
Table 12. ESD performance						
		\sim		Value		

Switching characteristics (T_A = 25 °C, V_{CC} = 3.3 V ±10%) Table 11

Table 12. ESD performance

Symbol	Test condition	Value			Unit
		Min	Тур	Max	Unit
ESD	Contact discharge ⁽¹⁾ IEC61000-4-2	-	±8	-	kV
	Human body model (JESD22-A114)	-	±8	-	kV

obsolete 1. Refer to Figure 3: Diagram for suggested VDD decoupling on page 10.



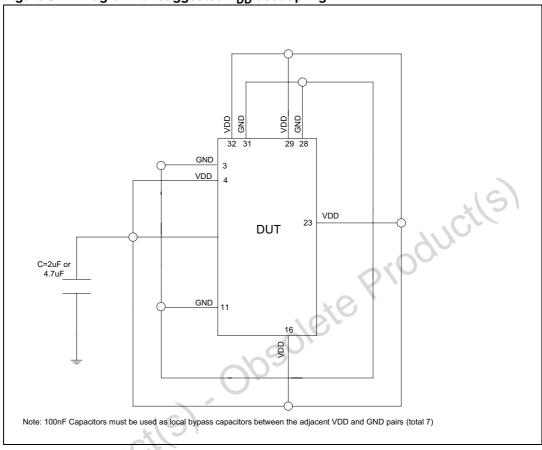
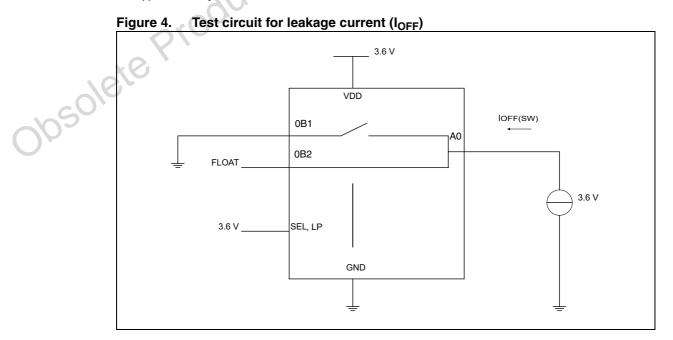


Figure 3. Diagram for suggested V_{DD} decoupling

1. Applicable for system level ESD test





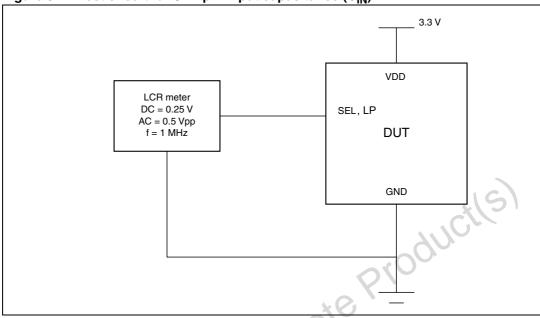
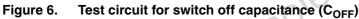
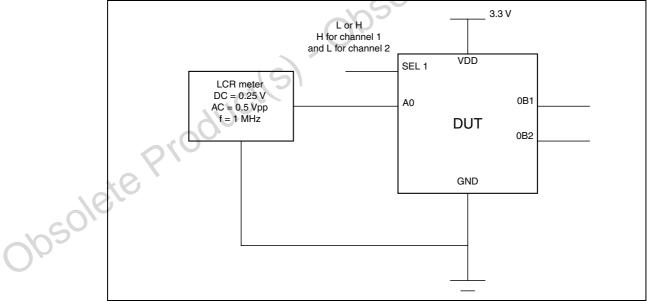


Figure 5. Test circuit for SEL pin input capacitance (CIN)







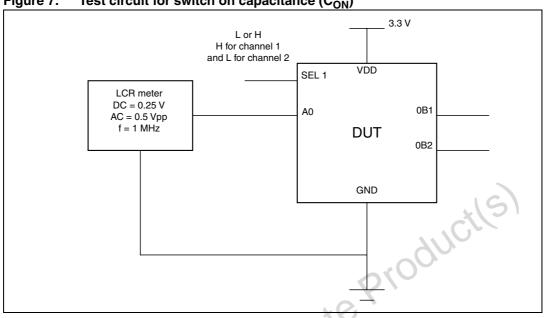
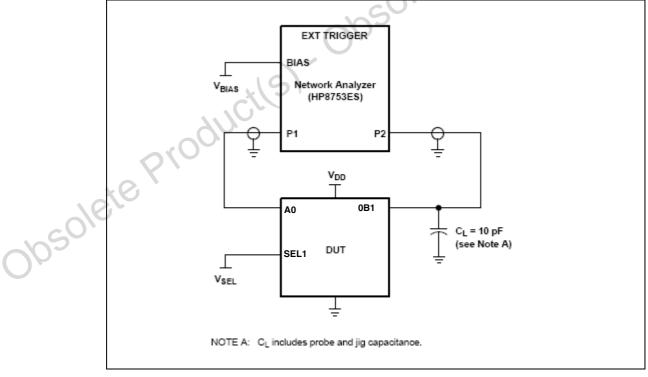


Figure 7. Test circuit for switch on capacitance (C_{ON})





Frequency response is measured at the output of the ON channel. For example, when $V_{SEL1} = 0$ and A0 is the input, the output is measured at 0B1. All unused analog I/O ports are left open.

HP8753ES setup:

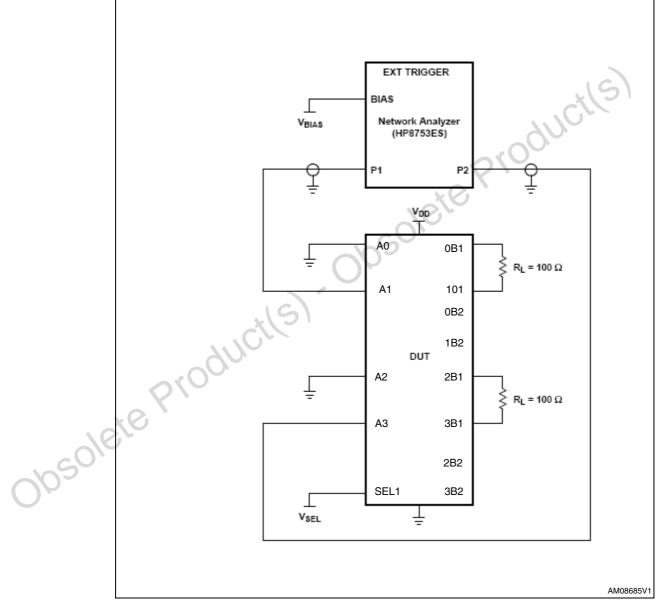
Average = 4

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 $R_{BW} = 3 \text{ kHz}$ $V_{BIAS} = 0.35 \text{ V}$ ST = 2 sP1 = 0 dBm





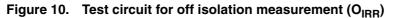
Crosstalk is measured at the output of the non-adjacent ON channel. For example, when $V_{SEL1} = 0$, and A1 is the input, the output is measured at A3. All unused analog input ports are connected to GND and output ports are left open.

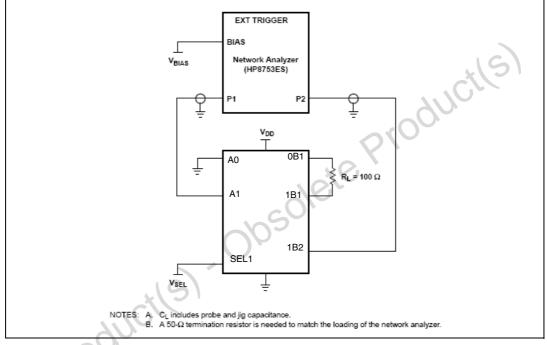
HP8753ES setup:

Average = 4



 $R_{BW} = 3 \text{ kHz}$ $V_{BIAS} = 0.35 \text{ V}$ ST = 2 sP1 = 0 dBm





Off isolation is measured at the output of the OFF channel. For example, when $V_{SEL1} = 0$, and A1 is the input, the output is measured at 1B2. All unused analog input ports are connected to GND and output ports are left open.

HP8753ES setup:

Average = 4 R_{BW} = 3 kHz V_{BIAS} = 0.35 V ST = 2 s P1 = 0 dBm



57

4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

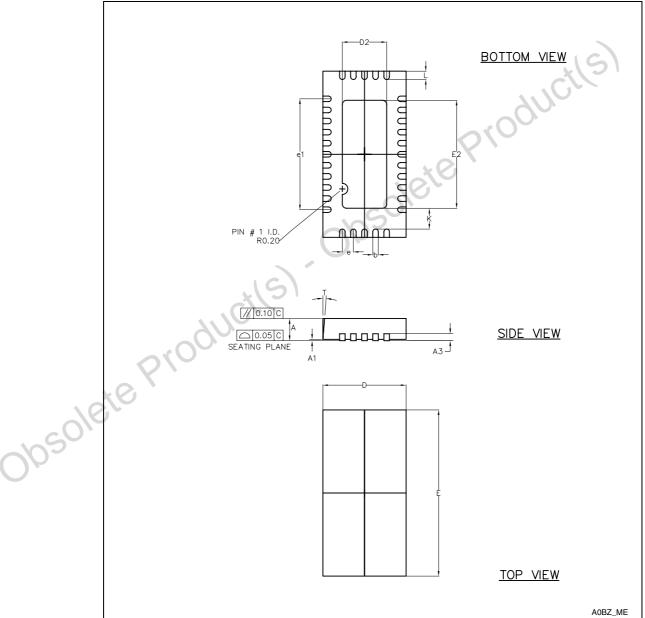


Figure 11. Package outline for QFN32L (3 x 6 x 0.8 mm) - pitch 0.4 mm

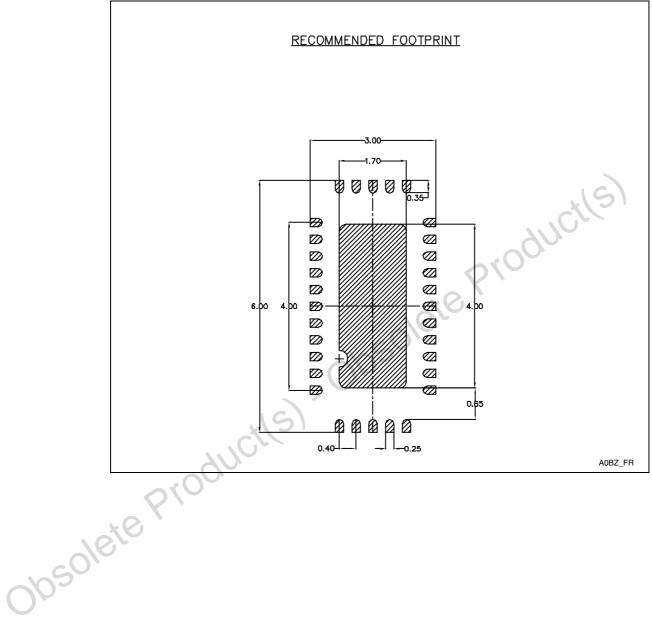
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Cumb al	Millimeters			
Symbol	Min	Тур	Max	
А	0.70	0.80	0.90	
A1	0.00	0.05	0.08	
A3		0.25		
Т	0.00		12.00	
b	0.15	0.20	0.25	
е		0.40	.(5)	
e1		4.00	CL	
К		0.75	90-	
D		3.00	$\mathcal{P}^{\mathcal{C}}$	
E		6.00		
L	0.25	0.30	0.35	
D2	1.50	1.60	1.79	
E2	3.80	3.90	4.00	
ate Produc				

Table 13. Mechanica	al data for QFN32L	(3 x 6 x 0.8 mm) - pitch 0.4 mm
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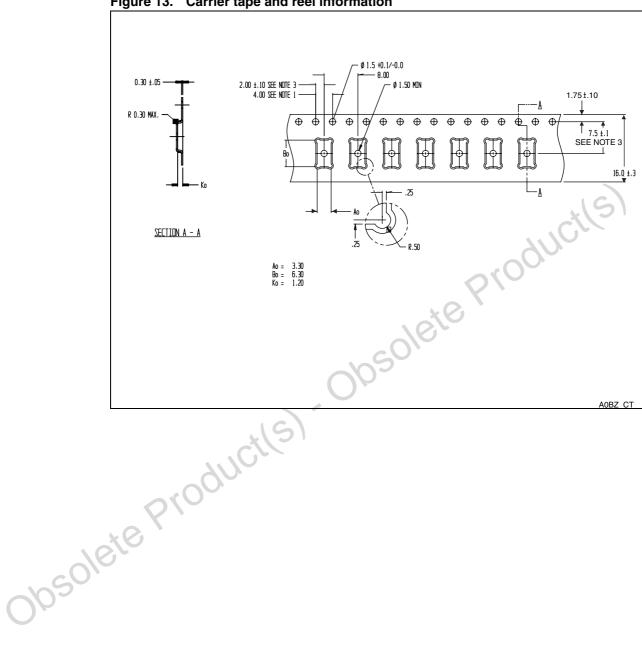


Figure 13. Carrier tape and reel information



5 Revision history

Table 14.Document revision history

	Date	Revision	Changes
	23-Apr-2010	1	Initial release.
	16-Jun-2010	2	Modified: <i>Figure 12</i> .
	09-Mar-2011	3	Updated: Table 8, Table 11 and Table 12.
obsole	tepto	ducil	Updated: Table 8, Table 11 and Table 12.



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